MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TK100A08N1

1. Applications

- Switching Voltage Regulators

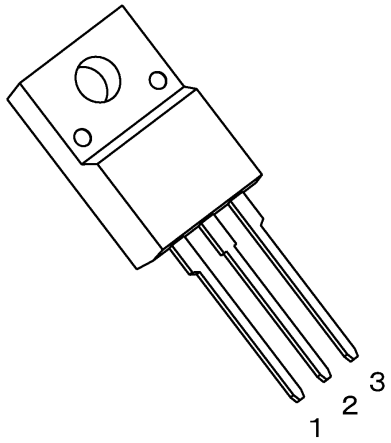
2. Features

(1) Low drain-source on-resistance: $R_{DS(ON)}$ = 2.6 mΩ (typ.) (V_{GS} = 10 V)

(2) Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 80 V)

(3) Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_D = 1.0 mA)

3. Packaging and Internal Circuit



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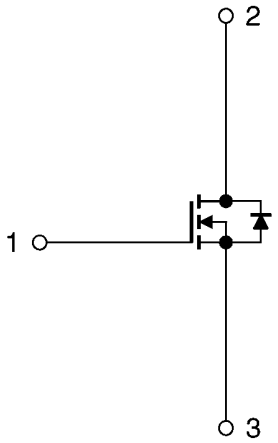

1: Gate
2: Drain
3: Source

4. Absolute Maximum Ratings (Note) (T_a = 25°C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	80	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)	(Silicon limit)	(Note 1,2)	I_D	214	A
Drain current (DC)	(T_c = 25°C)	(Note 1)	I_D	100	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I_{DP}	568	
Power dissipation	(T_c = 25°C)		P_D	45	W
Single-pulse avalanche energy		(Note 3)	E_{AS}	278	mJ
Avalanche current			I_{AR}	100	A
Channel temperature			T_{ch}	150	°C
Storage temperature			T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	—	—	±0.1	μA
Drain cut-off current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	I_D = 10 mA, V_{GS} = 0 V	80	—	—	V
Drain-source breakdown voltage (Note 4)	$V_{(BR)DSX}$	I_D = 10 mA, V_{GS} = -20 V	60	—	—	
Gate threshold voltage	V_{th}	V_{DS} = 10 V, I_D = 1.0 mA	2.0	—	4.0	
Drain-source on-resistance	$R_{DS(ON)}$	V_{GS} = 10 V, I_D = 50 A	—	2.6	3.2	mΩ

Note 4: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	V_{DS} = 40 V, V_{GS} = 0 V, f = 1 MHz	—	9000	—	pF
Reverse transfer capacitance	C_{rss}		—	52	—	
Output capacitance	C_{oss}		—	2100	—	
Gate resistance	r_g	—	—	3.2	—	Ω
Switching time (rise time)	t_r	See Figure 6.2.1	—	26	—	ns
Switching time (turn-on time)	t_{on}		—	53	—	
Switching time (fall time)	t_f		—	46	—	
Switching time (turn-off time)	t_{off}		—	140	—	

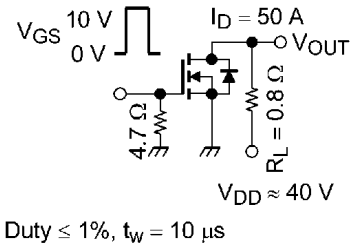

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V_{DD} ≈ 64 V, V_{GS} = 10 V, I_D = 100 A	—	130	—	nC
Gate-source charge 1	Q_{gs1}		—	45	—	
Gate-drain charge	Q_{gd}		—	33	—	
Gate switch charge	Q_{SW}		—	53	—	

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC)	(Note 5)	I_{DR}	—	—	—	100	A
Reverse drain current (pulsed)	(Note 5)	I_{DRP}	—	—	—	568	
Diode forward voltage		V_{DSF}	I_{DR} = 100 A, V_{GS} = 0 V	—	—	-1.2	V
Reverse recovery time	(Note 6)	t_{rr}	I_{DR} = 100 A, V_{GS} = 0 V $-dI_{DR}/dt$ = 100 A/μs	—	93	—	ns
Reverse recovery charge	(Note 6)	Q_{rr}		—	190	—	nC

Note 5: Ensure that the channel temperature does not exceed 150°C.
Note 6: Ensure that V_{DS} peak does not exceed V_{DSS}.

7. Marking (Note)

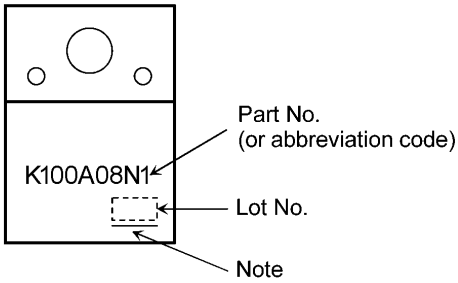

Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.
Not underlined: [[Pb]]/INCLUDES > MCV
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.
The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

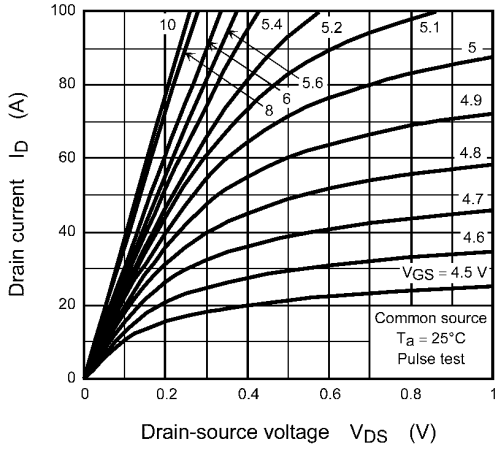

Fig. 8.1 I_D - V_{DS}

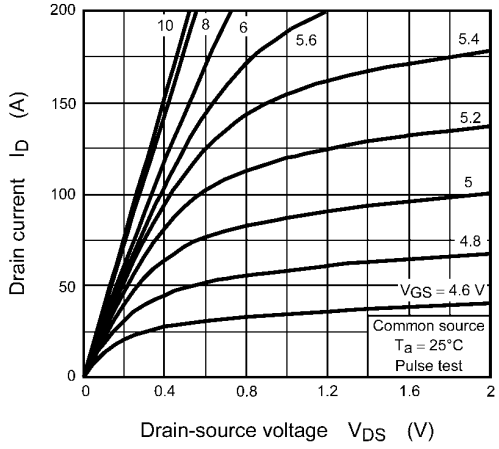

Fig. 8.2 I_D - V_{DS}

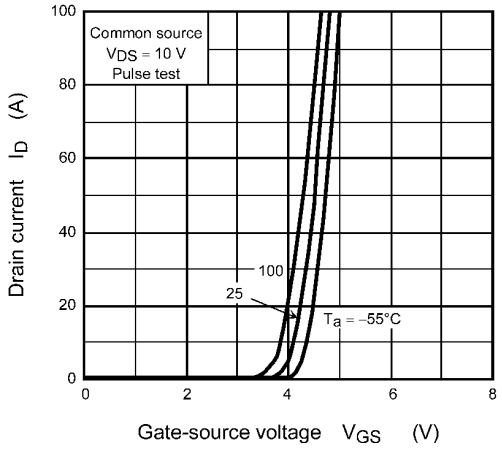

Fig. 8.3 I_D - V_{GS}

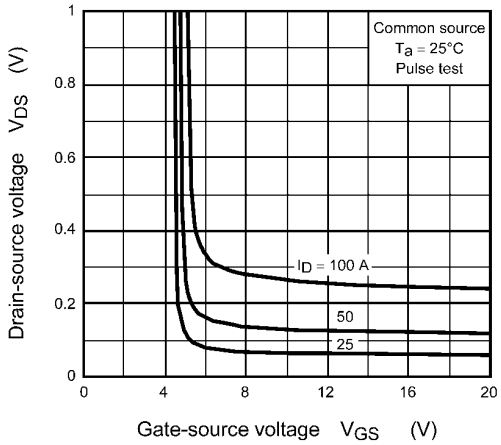

Fig. 8.4 V_{DS} - V_{GS}

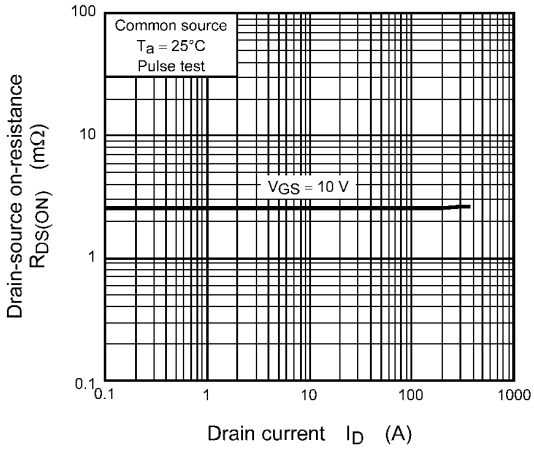

Fig. 8.5 $R_{DS(ON)}$ - I_D

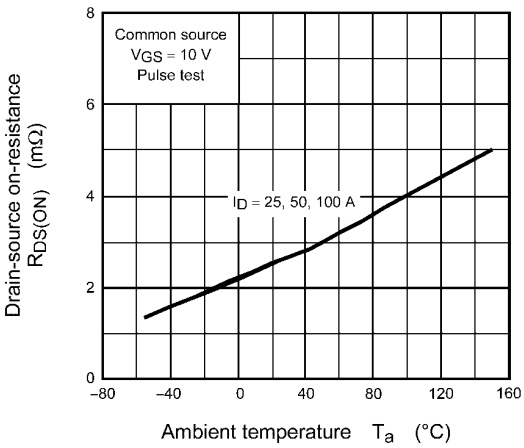

Fig. 8.6 $R_{DS(ON)}$ - T_a